

IN THE CLAIMS

Please amend the claims as follows:

1. (Canceled)
2. (Previously Presented) A method for forming a capacitor, comprising:
forming on a substrate assembly a conductive layer of a first material, the conductive layer having portions electrically isolated from one another;
forming a conformal metal layer of a second material atop the conductive layer; and
forming a dielectric by oxidizing at least a portion of the conformal metal layer.
3. (Previously Presented) The method as specified in Claim 2, further comprising forming a second conductive layer overlying the dielectric.
4. (Currently Amended) The method as specified in Claim 3, wherein forming the ~~second~~ conductive layer comprises depositing a material to form the conductive layer.
5. (Previously Presented) The method as specified in Claim 2, further comprising forming the conformal metal layer from at least one of titanium, copper, gold, tungsten and nickel.
6. (Previously Presented) The method as specified in Claim 2, further comprising applying a potential across an electrolytic solution and the conformal metal layer to oxidize said conformal metal layer.
- 7-9. (Canceled)
10. (Previously Presented) A method for fabricating a wafer, comprising:
forming a metal layer overlying a conductive layer of a starting substrate, the conductive layer having portions electrically isolated from one another; and

oxidizing the metal layer by applying a potential across an electrolytic solution and the metal layer.

11. (Previously Presented) A method of fabricating a wafer, comprising:

forming a metal layer of a first material overlying a first conductive layer of a second material formed on a starting substrate, the first conductive layer having portions electrically isolated from one another;

contacting the metal layer with an electrolytic solution;

applying a potential across the electrolytic solution and the metal layer; and

oxidizing at least a portion of the metal layer in response to said applying to form an oxidized layer.

12. (Previously Presented) The method as specified in Claim 11, wherein the first conductive layer includes polysilicon.

13. (Previously Presented) The method as specified in Claim 11, further comprising forming a second conductive layer overlying the oxidized layer.

14. (Previously Presented) The method as specified in Claim 11, wherein a non-oxidized portion of the metal layer and the first conductive layer form a conductive plate.

15. (Previously Presented) The method as specified in Claim 11, wherein applying the potential further comprises:

connecting a first electrode in contact with the electrolytic solution to a first terminal of a potential source; and

connecting the starting substrate to a second terminal of the potential source.

16. (Original) The method as specified in Claim 15, further comprising:

positioning a second electrode to contact the electrolytic solution; and

connecting the second electrode to the potential source.

17. (Original) The method as specified in Claim 11, further comprising the step of adjusting the potential across the electrolytic solution to control the oxidation of the metal layer.

18. (Original) The method as specified in Claim 17, further comprising:
monitoring a current in the electrolytic solution; and
adjusting the potential of the electrolytic solution to maintain a desired amount of the current.

19-28. (Canceled)

29. (Previously Presented) A method for forming a capacitor, comprising:
forming a first conductive layer of a first material, the first conductive layer having portions electrically isolated from one another;
forming a metal layer of a second material overlying the first conductive layer;
contacting the metal layer with an electrolytic solution;
applying a potential across the electrolytic solution and the metal layer; and
oxidizing at least a portion of the metal layer to form an oxidized layer in response to said applying, said oxidized layer forming at least a portion of a dielectric layer of the capacitor, and the first conductive layer forming a lower capacitor plate.

30. (Previously Presented) The method as specified in Claim 29, further comprising forming a second electrically conductive layer overlying the dielectric layer to form an upper capacitor plate.

31. (Canceled)

32. (Previously Presented) A method for forming a capacitor, comprising:
forming a conductive layer of a first material in contact with a starting substrate, the conductive layer having portions electrically isolated from one another;

forming a conformal metal layer of a second material overlying the conductive layer;
contacting the metal conformal layer with an electrolytic solution;
applying a potential across the electrolytic solution and the conformal metal layer;
conducting current in the electrolytic solution in response to applying the potential; and
oxidizing a portion of the conformal metal layer to form a metal oxide in response to said
conducting current, the metal oxide constituting a capacitor dielectric, and an unoxidized portion
of the conformal metal layer and the conductive layer constituting a first capacitor plate.

33. (Previously Presented) The method as specified in Claim 32, further comprising:
forming a second capacitor plate overlying the capacitor dielectric.

34. (Previously Presented) The method of Claim 32, wherein the conformal metal layer is an
initial metal layer and wherein the electrolytic solution is an initial electrolytic solution and
wherein the metal oxide is an initial metal oxide, and further comprising:

forming a further metal layer to overlying the initial metal oxide;
contacting the further metal layer with a further electrolytic solution;
applying a potential across the further electrolytic solution and the further metal layer;
conducting current in the further electrolytic solution in response to said applying a
potential across the further electrolytic solution; and

oxidizing, in response to said step of conducting current in the further electrolytic
solution, at least a portion of the further metal layer to form a further metal oxide, the further
metal oxide forming a further portion of the capacitor dielectric.

35. (Previously Presented) The method as specified in Claim 34, further comprising:
forming a second capacitor plate overlying the capacitor dielectric.

36. (Original) The method as specified in Claim 34, wherein the further electrolytic
solution and the initial electrolytic solution are the same solution.

37. (Previously Presented) A method for forming a capacitor, comprising:

forming an insulative layer overlying a substrate;
masking the insulative layer to define a region in which to fabricate the capacitor;
removing the insulative layer in an unmasked region to expose the substrate;
depositing a polysilicon layer overlying the insulative layer and the substrate and
contacting the substrate;
removing portions of the polysilicon layer to expose the insulative layer;
chemical vapor depositing a metal layer to overlie the polysilicon layer and the insulative
layer;
contacting the metal layer with an electrolytic solution;
applying an electrical potential to the electrolytic solution and the metal layer; and
oxidizing, in response to said applying, at least a portion of the metal layer to form a
metal oxide to function as a dielectric layer.

38. (Previously Presented) The method as specified in Claim 37, further comprising:
forming a conductive layer overlying the metal oxide layer.

39-49. (Previously Canceled)

50. (Previously Presented) The method of claim 38, wherein the metal layer includes
titanium.

51. (Previously Presented) The method as specified in Claim 38, wherein the metal layer
includes at least one of titanium, copper, gold, tungsten and nickel.

52. (Previously Presented) The method as specified in Claim 51, wherein the conductive
layer includes polysilicon.

53-75. (Canceled)

76. (Previously Presented) A method of forming a capacitor, comprising:

forming a polysilicon layer overlying a substrate, the polysilicon layer having portions electrically isolated from one another;

forming a conformal metal layer atop the portions of the polysilicon layer;

electrolytically oxidizing at least a portion of the conformal metal layer to form an oxidized portion; and

covering the oxidized portion with a conductive layer.

77. (Previously Added) The method as specified in claim 76, wherein forming the conformal metal layer includes depositing one of titanium, copper, gold, tungsten and nickel.